

参数表

2CLGA6KV-5mA 高压高频二极管采用高可靠性台面结构及扩散工艺,环氧树脂真空灌注密闭封装。

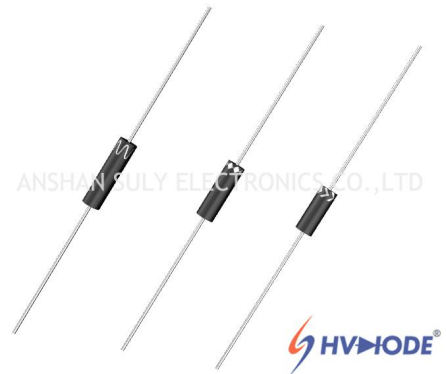
2CLGA6KV-5mA High voltage rectifier diode adopts high reliable mesa structure and diffusion craftwork, epoxy resin molded in a compact structure.

▼ 产品特点 Feature

- ❖ 雪崩电压击穿保护特性 Avalanche Characteristic
- ❖ 优异的抗浪涌电流冲击特性 Excellent surge current resistance
- ❖ 高速开关响应特性 High speed switch response characteristics
- ❖ 采用新型环氧树脂真空封装技术,表面具有抗腐蚀性
Epoxy resin molded in vacuum, have anticorrosion in the surface
- ❖ 工作结温 -50°C—+175°C Tj:50°C—+175°C
- ❖ 特殊耐高温性能芯片,可承受严酷恶劣的使用条件
Special high temperature resistant chip that can withstand harsh working conditions

▼ 产品 2D 图示

Graphical Representation

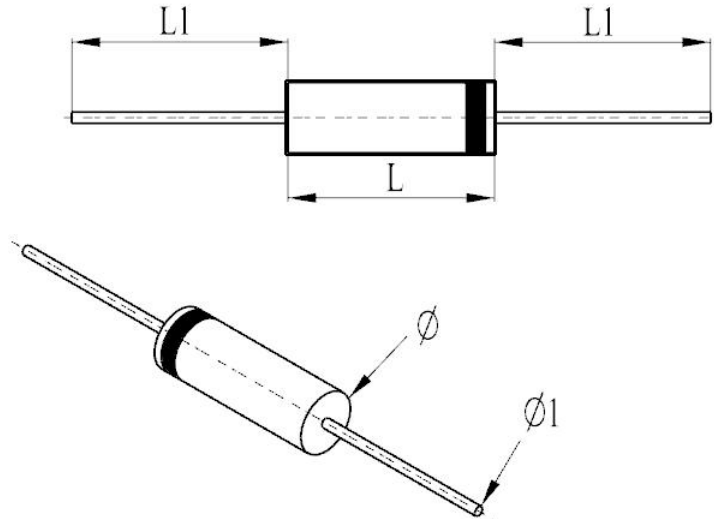


	参数名称 Item	符号 Symbol	单位 Unit	测试条件 Conditions	数值 Rating
Absolute Maximum Ratings 极限值 (绝对最大值)	反向重复峰值电压 Repetitive Peak Reverse Voltage	V_{RRM}	KV	Ta=25°C I _R =2.0μA	6.0
	反向工作峰值电压) Peak Working Reverse Voltage	V_{RWM}	KV	Ta=25°C I _R =2.0μA	6.0
	正向平均电流 Average Forward Current	$I_{F(AV)}$	mA	正弦半波 50Hz, 电阻负载, T _{break} =50°C (50Hz Half-sine Wave , Resistance load @T _{break} =50°C)	5.0
	反向恢复时间 Reverse Recovery Time	t _{rr}	nS		100
	正向(不重复)浪涌电流 Surge Forward Current	I_{FSM}	A	正弦半波持续时间 0.01S 50Hz 0.01S @ Half-Sine wave 50Hz	2.0
	工作环境温度 Operating Ambient Temperature	T _a	°C		-40 ~ +150
	存储温度 Storage Temperature	T _{stg}	°C		-40 ~ +120
Electrical Characteristics 电特性	正向峰值电压 Forward Peak Voltage	V_{FM}	V	@ Ta=25°C I _F =5mA	≥20.0
	反向峰值电流 Peak Reverse Current	I_{RRM1}	μA	@ Ta=25°C V _{RM} =V _{RRM}	2.0
		I_{RRM2}	μA	@ Ta=100°C V _{RM} =V _{RRM}	20.0

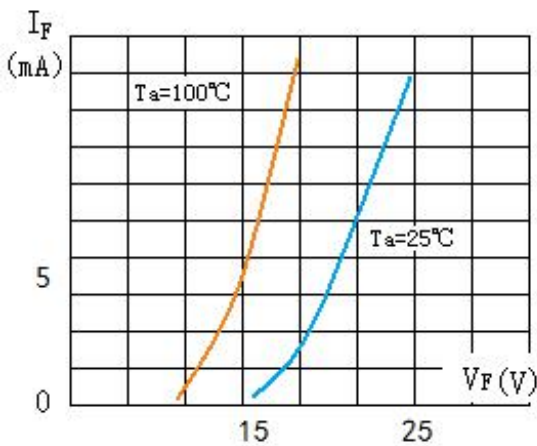
▼ 外形尺寸图示 Outline Drawings

(单位：毫米 mm)

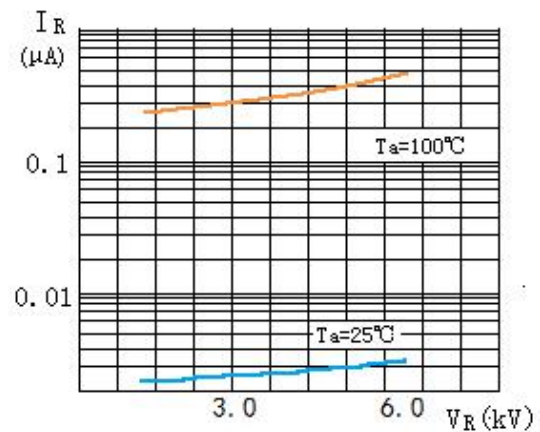
尺寸/ 图号	直径 (Φ)	长 (L)	线径 (Φ1)	线长 (L1)
Fig①	2	4.8	0.5	>20
Fig②	2.5	6.5	0.5	>20
Fig③	3	8	0.5	>20



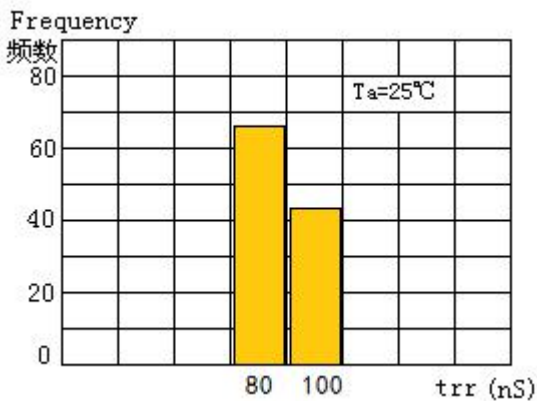
▼ 特性曲线图 Characteristic Curve



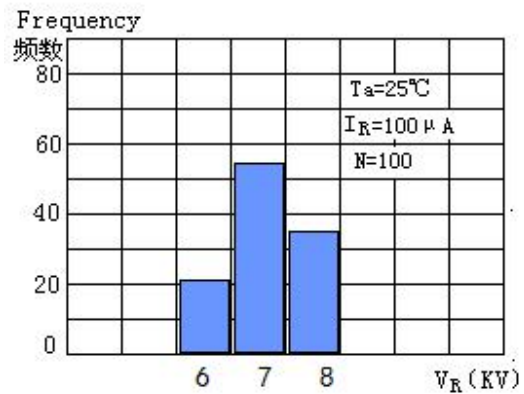
正向特性曲线 (2CLGA6KV-5mA)
Forward Characteristics



反向特性曲线 (2CLGA6KV-5mA)
Reverse Characteristics



反向恢复时间分布 (2CLGA6KV-5mA)
Reverse Recovery Time Distribution



反向雪崩电压分布 (2CLGA6KV-5mA)
Avalanche Breakdown Voltage